



PTO/SB/08a/b (08-03)

Approved for use through 07/31/2008. OMB 0651-0031

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/618,824-Conf. #5967 10/18/03
				Filing Date	February 27, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned LANDAU
				Attorney Docket Number	M4065.1006/P1006 B
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
ML	AA	US-6,673,648	01/06/2004	Lowrey	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

/Matthew Landau/

08/01/2006

2/27/2004

PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Not Yet Assigned 10/787123
				Filing Date	February 25, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned LANDAU
Sheet	1	of	12	Attorney Docket Number	M4065.1006/P1006-B

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
ME	AA	2002/0000666	1/2002	Kozicki et al.	
*	AB	2002/0072188	6/2002	Gilton	
*	AC	2002/0106849	08/2002	Moore	
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*	AJ	2002/0163828	11/2002	Krieger et al.	
*	AK	2002/0168852	11/2002	Harshfield et al.	
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*	AV	2003/0047773	03/2003	Li	
*	AW	2003/0049912	03/2003	Campbell et al.	
*	AX	2003/0068861	04/2003	Li	
*	AY	2003/0068862	04/2003	Li	
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*	AP1	4,269,935	5/1981	Masters et al.	
*	AQ1	4,312,938	1/1982	Drexler, et al.	
MI	AR1	4,316,946	1/1982	Masters, et al.	

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				Filing Date	February 25, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned Landau
Sheet	2	of	12	Attorney Docket Number	M4065.1006/P1006-B

ME	AS1	4,320,191	3/1982	Yoshikawa et al.	
*	AT1	4,405,710	9/1983	Balasubramanyam et al.	
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*	AX1	4,795,657	1/1989	Formigoni et al.	
*	AY1	4,800,526	01/1989	Lewis	
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*	AA2	5,177,567	1/1993	Klersy et al.	
*	AB2	5,219,788	6/1993	Abernathey et al.	
*	AC2	5,238,862	8/1993	Blalock et al.	
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*	AE2	5,314,772	5/1994	Kozicki	
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*	AI2	5,500,532	3/1996	Kozicki et al.	
*	AJ2	5,512,328	4/1996	Yoshimura et al.	
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*	AE3	6,300,684	10/2001	Gonzalez et al.	
*	AF3	6,316,784	11/2001	Zahorik et al.	
*	AG3	6,329,606	12/2001	Freyman et al.	
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not Yet Assigned 40/787/23
				Filing Date	February 25, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned Landau
				Attorney Docket Number	M4065.1006/P1006-B
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Not Yet Assigned 10/787123
				Filing Date	February 25, 2004
				First Named Inventor	Terry L. Gilton
				Art Unit	NTA 2815
				Examiner Name	Not Yet Assigned Landau
Sheet	4	of	12	Attorney Docket Number	M4065.1006/P1006-B

FOREIGN PATENT DOCUMENTS						
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
ML	BA	JP-56126916	10/1981	Akira et al.		
*	BB	WO 97/48032	12/18/1997	Kozicki et al.		
*	BC	WO 99/28914	06/10/1999	Kozicki et al.		
*	BD	WO 00/48196	8/17/00	Arizona Board of Regents		
ML	BE	WO 02/21542-A1	3/14/02	Axon Technologies Corp.		

Examiner Signature	/Matthew Landau/	Date Considered	08/01/2006
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	5	of	12	Attorney Docket Number	M4065.1006/P1006-B

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
ML	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.		
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*	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
*	CD	Affi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.		
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*	CF	Aleksieva, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
*	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
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*	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.		
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*	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, Thin solid films 70 (1980) L1-L4.		
*	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.		
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*	CT	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.		
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	6	of	12	Attorney Docket Number	M4065.1006/P1006-B

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	* CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
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	* CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
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		Filing Date	July 14, 2003		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	N/A		
		Examiner Name	Not Yet Assigned		
Sheet	7	of	12	Attorney Docket Number	M4065.1006/P1006-B

ML		silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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	CW1	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous GexSe _{1-x} photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.	
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	CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1996) 507-516.	
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	CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.	
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Examiner Signature	/Matthew Landau/	Date Considered	08/01/2006
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